

F.E. (Common)
PHYSICS
Applied Science - II
(2008 Pattern)

Time : 2 Hours]

[Max. Marks : 50]

Instructions to the candidates:

- 1) Answer any three (1 or 2, 3 or 4, 5 or 6) questions.
- 2) Figures to the right indicate full marks.
- 3) Neat diagrams must be drawn wherever necessary.
- 4) Use of logarithmic tables, slide rule, Mollier charts, electronic pocket calculator and steam tables is allowed.
- 5) Assume suitable data, if necessary.

Constants : $h = 6.63 \times 10^{-34}$ J.sec.

$$m_e = 9.1 \times 10^{-31} \text{ kg}$$

$$m_p = 1.67 \times 10^{-27} \text{ kg}$$

$$e = 1.6 \times 10^{-19} \text{ C}$$

$$c = 3 \times 10^8 \text{ m/sec.}$$

- Q1)** a) Derive the eigen energy formula and draw the first three wave functions for a particle confined in a rigid box? [7]
- b) Derive Schroedingers' time dependent wave equation. [6]
- c) A proton and an alpha particle are accelerated by the same P.D. find the relation between wavelengths of their corresponding matter waves. [4]

OR

- Q2)** a) Explain group velocity and phase velocity. Derive the expression with which a wave group travels. [7]
- b) State and illustrate Heisenberg's uncertainty principle by diffraction of electron. [6]
- c) An electron bound by a potential which closely approaches an infinite square well of width 1AU.

Calculate the lowest three permissible energies the electron can have.[4]

- Q3)** a) Draw a neat diagram of gas laser. Explain its principle, construction and working. [7]
- b) Explain following properties of superconductors: [6]
- i) Critical magnetic field
 - ii) Zero electrical resistance
- c) Explain Holography in brief. [4]

OR

- Q4)** a) Explain population inversion and spontaneous emission. Also write down the properties and applications of lasers. [7]
- b) With the help of energy band diagram explain construction and working of semiconductor Laser. [6]
- c) Explain Meissner effect in superconductors. [4]
- Q5)** a) Using Fermi Dirac probability distribution function, derive an expression for the position of Fermi energy level in the intrinsic semiconductor. [6]
- b) Explain the optical and electrical properties of nanoparticles. [6]
- c) An N type semiconductor is to have a resistivity 10 ohmcm. Calculate the number of donor atoms which must be added to achieve this. . [4]
($\mu_d = 500 \text{ cm}^2 / \text{VS}$)

OR

- Q6)** a) Explain Hall Effect in semiconductors. Derive the equation of hall voltage and hall co-efficient. [6]
- b) Explain synthesis of metal nanoparticles by colloidal route. [6]
- c) Calculate the conductivity of a germanium sample if one donor impurity is added to the extent of one part in 10^7 germanium atoms at room temperature. (Avagadro no. = 6.02×10^{23} , atomic wt.of Ge = 72.6, mobility of electrons = $3800 \text{ cm}^2/\text{VS}$, density of Ge = 5.32 gm/cc) [4]

